Icemos Technology Ltd Product Specification 1000.443401 Issue Date 05 October 2015 15:2

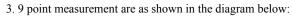
TO 1.37 4		
I Part Number	Customer	

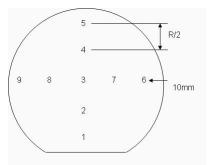
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Overall Thickness	660.00 +/- 26.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<80.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	600.00 +/- 25.00 μm	ADE, 100%
	14.0	Handle Doping Type	Р	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Lapped and etched with lasermarking	Guaranteed by Process
DeviceSilicon	19.0	Device Growth Method	CZ	Wafer Vendor
	20.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	21.0	Nominal Thickness	60.00 +/- 1.00 μm	ADE Single point, 100%
	22.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	23.0	Device Doping Type	N	Wafer Vendor
	24.0	Device Dopant	Phosphorous	Wafer Vendor
	25.0	Device Resistivity	1 - 10 Ohmem	Wafer Vendor
	26.0	Voids	none	Wafer Vendor
	27.0	Scratches	0	Bright Light, 100% (note 2)
	28.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Evolution, High intensity bright, Jamp inspection as per ASTM E523			

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information